Laurent Cario

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/344775/publications.pdf

Version: 2024-02-01

154 papers	4,927 citations	76196 40 h-index	110170 64 g-index
161 all docs	161 docs citations	161 times ranked	5967 citing authors

#	Article	IF	Citations
1	Artificial Electro-Optical Neuron Integrating Hot Electrons in a Mott Insulator. Physical Review Applied, 2022, 17, .	1.5	1
2	Correlated transition metal oxides and chalcogenides for Mott memories and neuromorphic applications. , 2022, , 307-360.		2
3	Nanoprobe study of the electric field driven insulator-to-metal transition in GaMo₄S₈. Journal of Physics: Conference Series, 2022, 2164, 012046.	0.3	0
4	Coherent and Incoherent Tunneling into Yu-Shiba-Rusinov States Revealed by Atomic Scale Shot-Noise Spectroscopy. Physical Review Letters, 2022, 128, .	2.9	9
5	Misfit Layer Compounds: A Platform for Heavily Doped 2D Transition Metal Dichalcogenides. Advanced Functional Materials, 2021, 31, 2007706.	7.8	17
6	Strain wave pathway to semiconductor-to-metal transition revealed by time-resolved X-ray powder diffraction. Nature Communications, 2021, 12, 1239.	5.8	29
7	<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>J</mml:mi><mml:mi>eff</mml:mi></mml: metallic phase and unconventional superconductivity in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>GaTa</mml:mi><mml:mn>4</mml:mn></ Physical Review B, 2021, 103, .	1.1	4
8	Design of metastable oxychalcogenide phases by topochemical (de)intercalation of sulfur in La2O2S2. Nature Communications, 2021, 12, 3605.	5.8	12
9	Mapping metal/insulator nanodomains switching in V2O3 by variable-temperature electron spectromicroscopy investigations. Microscopy and Microanalysis, 2021, 27, 1482-1485.	0.2	0
10	Solvothermal and mechanochemical intercalation of Cu into La₂O₂S₂ enabled by the redox reactivity of (S₂)^{2â^'} pairs. Dalton Transactions, 2021, 50, 12419-12423.	1.6	3
11	Photoinduced charge density wave phase in 1T-TaS<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mrow /> <mml:mn>2</mml:mn> </mml:msub></mml:math>: growth and coarsening mechanisms. Comptes Rendus Physique, 2021, 22, 139-160.	0.3	2
12	Probing and Mapping the Dynamics of Metal/Insulator Nanodomains Switching in V2O3 by Cryo-Spectromicroscopy Techniques. Microscopy and Microanalysis, 2021, 27, 67-68.	0.2	0
13	Extreme in-plane upper critical magnetic fields of heavily doped quasi-two-dimensional transition metal dichalcogenides. Physical Review B, 2021, 104, .	1.1	11
14	Structure of the water-splitting photocatalyst oxysulfide Î±-LaOInS₂ and ab initio prediction of new polymorphs. Chemical Communications, 2020, 56, 1645-1648.	2.2	20
15	Prediction of a New Layered Polymorph of FeS₂ with Fe³⁺S^{2â€“}(S₂^{2â€“})_{1/2} Structure. Journal of Physical Chemistry Letters, 2020, 11, 8861-8866.	2.1	7
16	Control of stoichiometry and morphology in polycrystalline V2O3 thin films using oxygen buffers. Journal of Materials Science, 2020, 55, 14717-14727.	1.7	2
17	Competition between V2O3 phases deposited by one-step reactive sputtering process on polycrystalline conducting electrode. Thin Solid Films, 2020, 705, 138063.	0.8	7
18	Periodic Surface Modulation of (LaSe)_{1.14}(NbSe₂) Observed by Scanning Tunneling Microscopy. Acta Physica Polonica A, 2020, 137, 785-787.	0.2	2

#	Article	IF	Citations
19	Unusually long carrier lifetime in a Mott insulator revealed by time-resolved Photoemission Electron Microscopy. , 2020, , .		0
20	Impact of Nanostructuration on the Chemical Composition of Nickel Oxide Nanoparticles. Inorganic Chemistry, 2019, 58, 15004-15007.	1.9	4
21	THz Driven Dynamics in Mott Insulator GaTa₄ Se₈. , 2019, , .		1
22	Preparation by electrophoretic deposition of molybdenum iodide cluster-based functional nanostructured photoelectrodes for solar cells. Electrochimica Acta, 2019, 317, 737-745.	2.6	21
23	Unexplored reactivity of (S_n)^{2â^'} oligomers with transition metals in low-temperature solid-state reactions. Chemical Communications, 2019, 55, 6189-6192.	2.2	7
24	Higgs-mode radiance and charge-density-wave order in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>2</mml:mn><mml:mi>H</mml:mi><mml:mo>â^'</mml:m Physical Review B, 2018, 97, .	1.1	41
25	Non-volatile resistive switching in the Mott insulator (V1â^'xCrx)2O3. Physica B: Condensed Matter, 2018, 536, 327-330.	1.3	9
26	A Topochemical Approach to Synthesize Layered Materials Based on the Redox Reactivity of Anionic Chalcogen Dimers. Angewandte Chemie, 2018, 130, 13806-13811.	1.6	1
27	Mott insulators: A large class of materials for Leaky Integrate and Fire (LIF) artificial neuron. Journal of Applied Physics, 2018, 124, .	1.1	24
28	Relaxation of a Spiking Mott Artificial Neuron. Physical Review Applied, 2018, 10, .	1.5	14
29	Traces of charge density waves in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>NbS</mml:mi><mml:mn>2</mml:mn></mml:msub></m Physical Review B, 2018, 97, .	1.1	41
30	First demonstration of â€œLeaky Integrate and Fireâ€•artificial neuron behavior on (V0.95Cr0.05)2O3 thin film. MRS Communications, 2018, 8, 835-841.	0.8	11
31	Mott Memory Devices Based on the Mott Insulator (V1-xCrx)2O3. , 2018, , .		1
32	How a dc Electric Field Drives Mott Insulators Out of Equilibrium. Physical Review Letters, 2018, 121, 016601.	2.9	33
33	Cu2O@CuO core-shell nanoparticles as photocathode for p-type dye sensitized solar cell. Journal of Alloys and Compounds, 2018, 769, 605-610.	2.8	26
34	A Topochemical Approach to Synthesize Layered Materials Based on the Redox Reactivity of Anionic Chalcogen Dimers. Angewandte Chemie - International Edition, 2018, 57, 13618-13623.	7.2	15
35	Coherent phonon dynamics in misfit-layered chalcogenide LaVS3 crystal. , 2018, , .		0
36	Combined First-Principles Calculations and Experimental Study of the Phonon Modes in the Multiferroic Compound GeV₄S₈. Journal of Physical Chemistry C, 2017, 121, 3522-3529.	1.5	10

#	Article	IF	Citations
37	A Leakyâ€Integrateâ€andâ€Fire Neuron Analog Realized with a Mott Insulator. Advanced Functional Materials, 2017, 27, 1604740.	7.8	186
38	Engineering Processes at the Interface of pâ€Semiconductor for Enhancing the Open Circuit Voltage in pâ€Type Dyeâ€Sensitized Solar Cells. Advanced Energy Materials, 2017, 7, 1601776.	10.2	36
39	(Invited) Control of Resistive Switching in Mott Memories Based on TiN/AM4Q8/TiN MIM Devices. ECS Transactions, 2017, 75, 3-12.	0.3	2
40	A p-Type Zinc-Based Metalâ€“Organic Framework. Inorganic Chemistry, 2017, 56, 6208-6213.	1.9	9
41	An Artificial Neuron Founded on Resistive Switching of Mott Insulators. , 2017, , .		1
42	Direct experimental observation of the molecular J effâ€‰=â€‰3/2 ground state in the lacunar spinel GaTa4Se8. Nature Communications, 2017, 8, 782.	5.8	30
43	Domain-size effects on the dynamics of a charge density wave in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>1</mml:mn><mml:mi mathvariant="normal">T</mml:mi><mml:mtext>â^’</mml:mtext><mml:msub><mml:mi>TaS</mml:mi><mml:mn>2</mml:mn></mml:m Physical Review B, 2017, 96, .	3.7	13
44	Crystal structure and chemical bonding in the mixed anion compound BaSF. Dalton Transactions, 2017, 46, 16244-16250.	1.6	11
45	Ultrafast Formation of a Charge Density Wave State in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mn>1</mml:mn><mml:mi>T</mml:mi><mml:mtext>â^’</mml:mtext><mml:msub><mml:mrow><m : Observation at Nanometer Scales Using Time-Resolved X-Ray Diffraction. Physical Review Letters, 2017, 118, 247401.	8.6	60
46	Experimental and Theoretical Evidences of p-Type Conductivity in Nickel Carbodiimide Nanoparticles with a Delafossite Structure Type. Inorganic Chemistry, 2017, 56, 7922-7927.	1.9	14
47	Inorganic Molybdenum Clusters as Lightâ€Harvester in All Inorganic Solar Cells: A Proof of Concept. ChemistrySelect, 2016, 1, 2284-2289.	0.7	35
48	CuO nanomaterials for p-type dye-sensitized solar cells. RSC Advances, 2016, 6, 112765-112770.	1.7	46
49	Strong enhancement of superconductivity at high pressures within the charge-density-wave states of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>2</mml:mn><mml:mi>H</mml:mi><mml:mtext>â^’</mml:m xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>2</mml:mn><mml:mi>H</mml:mi><mml:mtext>â^’</mml:m Physical Review B, 2016, 93, .	3.7	26
50	Modulation of Defects in Semiconductors by Facile and Controllable Reduction: The Case of p-type CuCrO₂ Nanoparticles. Inorganic Chemistry, 2016, 55, 7729-7733.	1.9	20
51	Metalâ€“insulator transitions in (V1-xCrx)2O3 thin films deposited by reactive direct current magnetron co-sputtering. Thin Solid Films, 2016, 617, 56-62.	0.8	17
52	Ba₂F₂Fe_{1.5}Se₃: An Intergrowth Compound Containing Iron Selenide Layers. Inorganic Chemistry, 2016, 55, 2923-2928.	1.9	7
53	Preparation of nitrogen doped zinc oxide nanoparticles and thin films by colloidal route and low temperature nitridation process. Solid State Sciences, 2016, 54, 30-36.	1.5	19
54	Copper borate as a photocathode in p-type dye-sensitized solar cells. RSC Advances, 2016, 6, 1549-1553.	1.7	41

#	Article	IF	Citations
55	Synthesis of Ni-poor NiO nanoparticles for p-DSSC applications. Solid State Sciences, 2016, 54, 37-42.	1.5	21
56	Unravelling the origin of the giant Zn deficiency in wurtzite type ZnO nanoparticles. Scientific Reports, 2015, 5, 12914.	1.6	17
57	Quasiparticle spectra of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>2</mml:mn><mml:mi>H</mml:mi><mml:mo>â€'</mml:m… Two-band superconductivity and the role of tunneling selectivity. Physical Review B, 2015, 92, .	1.1	56
58	Strong anharmonicity induces quantum melting of charge density wave in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>2</mml:mn><mml:mi>H</mml:mi><mml:mo>â€'</mml:m… pressure. Physical Review B, 2015, 92, .	1.1	93
59	Control of resistive switching in AM₄Q₈narrow gap Mott insulators: A first step towards neuromorphic applications. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 239-244.	0.8	18
60	Resistive Switching in Mott Insulators and Correlated Systems. Advanced Functional Materials, 2015, 25, 6287-6305.	7.8	130
61	Negative Colossal Magnetoresistance Driven by Carrier Type in the Ferromagnetic Mott Insulator GaV₄S₈. Chemistry of Materials, 2015, 27, 4398-4404.	3.2	13
62	Resistive Switching Induced by Electric Pulses in a Single-Component Molecular Mott Insulator. Journal of Physical Chemistry C, 2015, 119, 2983-2988.	1.5	15
63	The first dye-sensitized solar cell with p-type LaOCuS nanoparticles as a photocathode. RSC Advances, 2015, 5, 60148-60151.	1.7	20
64	From Resistive Switching Mechanisms in AM4Q8 Mott Insulators to Mott Memories. , 2015, , .		0
65	X-ray study of femtosecond structural dynamics in the 2D charge density wave compound 1T-TaS2. Physica B: Condensed Matter, 2015, 460, 100-104.	1.3	14
66	Coherent long-range magnetic bound states in aÂsuperconductor. Nature Physics, 2015, 11, 1013-1016.	6.5	155
67	Amplitude Higgs mode in the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mn>2</mml:mn><mml:mi>H</mml:mi><mml:mo>âˆ'</mml:mo><mml:m… Physical Review B, 2014, 89, .	1.1	124
68	Electric Pulse Induced Resistive Switching in the Narrow Gap Mott Insulator GaMo₄S₈. Key Engineering Materials, 2014, 617, 135-140.	0.4	10
69	Impact of Mg Doping on Performances of CuGaO₂ Based p-Type Dye-Sensitized Solar Cells. Journal of Physical Chemistry C, 2014, 118, 54-59.	1.5	47
70	Orbital-Ordering-Driven Multiferroicity and Magnetoelectric Coupling in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>GeV</mml:mi></mml:mrow><mml:mrow><mml:mn>4</mml:mn></m… mathvariant="normal">S</mml:mi></mml:mrow><mml:mrow><mml:mn>8</mml:mn></mml:mrow></mml:msub></mml:mrow></mml:… Physical Review Letters, 2014, 113, 137602.	2.9	51
71	First-Order Insulator-to-Metal Mott Transition in the Paramagnetic 3D System<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>GaTa</mml:mi></mml:mrow><mml:mrow><mml:mn>4</mml:mn>… Physical Review Letters, 2014, 113, 086404.	2.9	52
72	Relation between Thermally Induced Structural Distortions and Electronic Properties of the Layered Misfit Chalcogenide (LaS)1.196VS2. Journal of Physical Chemistry C, 2014, 118, 19273-19279.	1.5	5

#	Article	IF	Citations
73	Nonthermal and purely electronic resistive switching in a Mott memory. Physical Review B, 2014, 90, .	1.1	44
74	Deposition of GaV₄S₈ thin films by H₂S/Ar reactive sputtering for ReRAM applications. Journal Physics D: Applied Physics, 2014, 47, 065309.	1.3	7
75	Resistive Switching at the Nanoscale in the Mott Insulator Compound GaTa₄Se₈. Nano Letters, 2013, 13, 3648-3653.	4.5	62
76	Universal Electricâ€Fieldâ€Driven Resistive Transition in Narrowâ€Gap Mott Insulators. Advanced Materials, 2013, 25, 3222-3226.	11.1	114
77	Electric field induced avalanche breakdown and non-volatile resistive switching in the Mott Insulators AM4Q8. European Physical Journal: Special Topics, 2013, 222, 1046-1056.	1.2	14
78	Hole conductivity and acceptor density of p-type CuGaO2 nanoparticles determined by impedance spectroscopy: The effect of Mg doping. Electrochimica Acta, 2013, 113, 570-574.	2.6	43
79	Deposition by radio frequency magnetron sputtering of GaV4S8 thin films for resistive random access memory application. Thin Solid Films, 2013, 533, 54-60.	0.8	9
80	Origin of the Black Color of NiO Used as Photocathode in p-Type Dye-Sensitized Solar Cells. Journal of Physical Chemistry C, 2013, 117, 22478-22483.	1.5	76
81	Avalanche breakdown in GaTa4Se8â^'xTex narrow-gap Mott insulators. Nature Communications, 2013, 4, 1722.	5.8	100
82	Scanning tunneling measurements of layers of superconducting 2<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>H</mml:mi></mml:math>-TaSe<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>: Evidence for a zero-bias anomaly in single layers. Physical Review B, 2013, 87, .	1.1	33
83	Electrical characterizations of resistive random access memory devices based on GaV4S8 thin layers. Thin Solid Films, 2013, 533, 61-65.	0.8	19
84	Pressure dependence of superconducting critical temperature and upper critical field of 2<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>H</mml:mi></mml:math>-NbS<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>. Physical Review B, 2013, 87, .	1.1	63
85	Optical Conductivity Measurements of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>GaTa</mml:mi><mml:mn>4</mml:mn></mml:msub><mml:msub><mml:mi>Se</mml:mi><mml:mn> High Pressure: Evidence of a Bandwidth-Controlled Insulator-to-Metal Mott Transition. Physical Review Letters, 2013, 110, 037401.	2.9	49
86	Mott-memories Based on the Narrow Gap Mott Insulators AM4Q8 (A=Ga, Ge ; M = V, Nb, Ta ; Q = S, Se). Materials Research Society Symposia Proceedings, 2013, 1562, 1.	0.1	0
87	Ultrafast filling of an electronic pseudogap in an incommensurate crystal. Physical Review B, 2013, 87, .	1.1	14
88	Anharmonic suppression of charge density waves in 2<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>H</mml:mi></mml:mrow></mml:math>-NbS<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>. Physical Review B, 2012, 86, .	1.1	66
89	CuGaO2: a promising alternative for NiO in p-type dye solar cells. Journal of Materials Chemistry, 2012, 22, 14353.	6.7	114
90	P-Type Nitrogen-Doped ZnO Nanoparticles Stable under Ambient Conditions. Journal of the American Chemical Society, 2012, 134, 464-470.	6.6	115

#	Article	IF	Citations
91	High-pressure X-ray diffraction study of 1T-TaS2. Physica B: Condensed Matter, 2012, 407, 1704-1706.	1.3	12
92	Anisotropy and temperature dependence of the first critical field in 2Hâ€“NbS2. Physica B: Condensed Matter, 2012, 407, 1813-1815.	1.3	11
93	Control of the Electronic Properties and Resistive Switching in the New Series of Mott Insulators GaTa₄Se_{8â€“y}Te_y (0 â‰¤ y â‰¤ 6.5). Chemistry of Materials, 2011, 23, 2611-2618.	3.2	28
94	Temperature and size dependence of time-resolved exciton recombination in ZnO quantum dots. Applied Physics Letters, 2011, 99, .	1.5	18
95	In-plane magnetic penetration depth in NbS2. Physical Review B, 2011, 84, .	1.1	14
96	First evidence of resistive switching in polycrystalline GaV₄S₈ thin layers. Physica Status Solidi - Rapid Research Letters, 2011, 5, 53-55.	1.2	23
97	Ruthenium polypyridine complexes as sensitizers in NiO based p-type dye-sensitized solar cells: Effects of the anchoring groups. Journal of Photochemistry and Photobiology A: Chemistry, 2011, 219, 235-242.	2.0	117
98	Chiral charge order in the superconductor 2H-TaS₂. New Journal of Physics, 2011, 13, 103020.	1.2	45
99	Studies on two-gap superconductivity in 2Hâ€“NbS2. Physica C: Superconductivity and Its Applications, 2010, 470, S719-S720.	0.6	5
100	Electricâ€Fieldâ€Induced Resistive Switching in a Family of Mott Insulators: Towards a New Class of RRAM Memories. Advanced Materials, 2010, 22, 5193-5197.	11.1	125
101	Synthesis of lightâ€coloured nanoparticles of wide band gap pâ€type semiconductors CuGaO₂ and LaOCuS by low temperature hydro/solvothermal processes. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1642-1646.	0.8	9
102	Synthesis of p-Type Transparent LaOCuS Nanoparticles via Soft Chemistry. Inorganic Chemistry, 2010, 49, 3074-3076.	1.9	29
103	Half-Metallic Ferromagnetism and Large Negative Magnetoresistance in the New Lacunar Spinel GaTi₃VS₈. Journal of the American Chemical Society, 2010, 132, 5704-5710.	6.6	55
104	Specific heat measurements of a superconducting<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>NbS</mml:mtext></mml:mrow><mml:mn>2</mml:mn></mml:ms crystal in an external magnetic field: Energy gap structure. Physical Review B, 2010, 82, .	1.1	52
105	Two-Gap Superconductivity in 2H-NbS₂. Acta Physica Polonica A, 2010, 118, 1024-1025.	0.2	5
106	Electricâ€Fieldâ€Assisted Nanostructuring of a Mott Insulator. Advanced Functional Materials, 2009, 19, 2800-2804.	7.8	23
107	Simple and Reproducible Procedure to Prepare Self-Nanostructured NiO Films for the Fabrication of P-Type Dye-Sensitized Solar Cells. Inorganic Chemistry, 2009, 48, 8245-8250.	1.9	85
108	Thin Layers Obtained by Plasma Process for Emerging Non-Volatile Memory (RRAM) Applications. , 2009, , .		3

#	Article	IF	Citations
109	Electricâ€Pulseâ€driven Electronic Phase Separation, Insulatorâ€“Metal Transition, and Possible Superconductivity in a Mott Insulator. Advanced Materials, 2008, 20, 2760-2765.	11.1	70
110	Electric-pulse-induced resistive switching and possible superconductivity in the Mott insulator GaTa4Se8. Microelectronic Engineering, 2008, 85, 2430-2433.	1.1	28
111	Tuning the size and color of the p-type wide band gap delafossite semiconductor CuGaO2 with ethylene glycol assisted hydrothermal synthesis. Journal of Materials Chemistry, 2008, 18, 5647.	6.7	87
112	Superconducting Density of States and Vortex Cores of 2H-<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>NbS</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:math>. Physical Review Letters, 2008, 101, 166407.	2.9	183
113	Structure and Magnetic Properties of Oxychalcogenides A₂F₂Fe₂OQ₂(A = Sr, Ba; Q = S, Se) with Fe₂O Square Planar Layers Representing an Antiferromagnetic Checkerboard Spin Lattice. Journal of the American Chemical Society, 2008, 130, 8261-8270.	6.6	105
114	Ba2F2Fe2+0.5Fe3+S3: A Two-Dimensional Inhomogeneous Mixed Valence Iron Compound. Inorganic Chemistry, 2008, 47, 1648-1652.	1.9	11
115	Metalâ^'Metal Bonding and Correlated Metallic Behavior in the New Deficient Spinel Ga0.87Ti4S8. Chemistry of Materials, 2008, 20, 2382-2387.	3.2	27
116	Cation Deficient Layered Ruddlesdenâ^'Popper-Related Oxysulfides La₂LnMS₂O₅ (Ln = La, Y; M = Nb, Ta). Inorganic Chemistry, 2007, 46, 9584-9590.	1.9	19
117	Facile Synthesis of BiCuOS by Hydrothermal Methods. Inorganic Chemistry, 2007, 46, 10741-10748.	1.9	55
118	Self-Assembly and Characterization of Layered Double Hydroxide/DNA Hybrids. Nano Letters, 2006, 6, 199-204.	4.5	266
119	P-type transparent conductors Sr1â^'xNaxFCuS and SrF1â^'xOxCuS: design, synthesis and physical properties. Journal of Materials Chemistry, 2006, 16, 4165-4169.	6.7	22
120	Design of a New Family of Inorganic Compounds Ae2F2SnX3(Ae = Sr, Ba; X = S, Se) Using Rock Salt and Fluorite 2D Building Blocks. Inorganic Chemistry, 2006, 45, 917-922.	1.9	33
121	Dielectric breakdown and current switching effect in the incommensurate layered compound(LaS)1.196VS2. Physical Review B, 2006, 73, .	1.1	20
122	Ae2Sb2X4F2(Ae = Sr, Ba):Â New Members of the Homologous Series Ae2M1+nX3+nF2Designed from Rock Salt and Fluorite 2D Building Blocks. Inorganic Chemistry, 2006, 45, 2713-2717.	1.9	32
123	Rational conception of inorganic compounds using 2D secondary building units. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2867-2870.	0.8	2
124	Synthesis and crystal structure of a new oxychalcogenide La5Tiâ^¼3.25Zrâ^¼0.25S5O9.25. Journal of Solid State Chemistry, 2005, 178, 1637-1643.	1.4	3
125	Designing New Inorganic Compounds from 2D Building Blocks. Chemistry of Materials, 2005, 17, 234-236.	3.2	45
126	Determination of the modulated structure of the misfit layer compound (LaS)1.196VS2. Materials Research Bulletin, 2005, 40, 125-133.	2.7	14

#	Article	IF	Citations
127	Design and magnetic properties of new compounds containing iron 2D building blocks of the perovskite type. Solid State Sciences, 2005, 7, 936-944.	1.5	22
128	Design and Magnetic Properties of New Compounds Containing Iron 2D Building Blocks of the Perovskite Type.. ChemInform, 2005, 36, no.	0.1	0
129	Rational design of new inorganic compounds with the ZrSiCuAs structure type using 2D building blocks. Journal of Materials Chemistry, 2005, 15, 3525.	6.7	55
130	Crystal structure and electrical properties of the mixed valent titanium oxysulfide Sm2Ti2S2O4.5. Journal of Solid State Chemistry, 2004, 177, 2464-2469.	1.4	3
131	Crystal structures of two new oxysulfides La5Ti2MS5O7 (M=Cu, Ag): evidence of anionic segregation. Journal of Solid State Chemistry, 2004, 177, 2810-2817.	1.4	49
132	Synthesis, X-ray and optical characterizations of two new oxysulfides: LaInS2O and La5In3S9O3. Journal of Solid State Chemistry, 2004, 177, 1053-1059.	1.4	17
133	A Mixed-Valent Niobium Oxysulfide, La2Nb3S2O8.. ChemInform, 2003, 34, no.	0.1	0
134	A mixed-valent niobium oxysulfide, La2Nb3S2O8. Acta Crystallographica Section C: Crystal Structure Communications, 2003, 59, i55-i56.	0.4	7
135	A new lanthanum titanium oxysulfide, La16Ti5S17+xO17, withxâ€…=â€…0.75â€…(9). Acta Crystallographica Section C: Crystal Structure Communications, 2003, 59, i63-i64.	0.4	4
136	A gadolinium and niobium oxide sulfide, Gd3NbS3O4. Acta Crystallographica Section E: Structure Reports Online, 2003, 59, i101-i102.	0.2	5
137	Mixed-Valence State of Europium in the Misfit Layer Compound (EuS)1.173NbS2. Chemistry of Materials, 2003, 15, 943-950.	3.2	23
138	Synthesis and Physical Properties of Co-intercalated Layered Lanthanide Oxychlorides LixTHFyLnOCl (Ln = Y, Lu). Chemistry of Materials, 2003, 15, 4325-4331.	3.2	3
139	Structural studies of a cubic, high-temperature (Î±) polymorph of Pb2GeS4 and the isostructural Pb2â^'xSnxGeS4â^'ySey solid solution. Journal of Alloys and Compounds, 2002, 335, 105-110.	2.8	22
140	Synthesis and crystal structure of two new oxychalcogenides: Eu5V3S6O7 and La10Se14O. Materials Research Bulletin, 2002, 37, 1895-1905.	2.7	10
141	Ln3T2N6 (Ln=La, Ce, Pr; T=Ta, Nb), a New Family of Ternary Nitrides Isotypic to a High Tc Cuprate Superconductor. Journal of Solid State Chemistry, 2001, 162, 90-95.	1.4	23
142	Charge Transfer in Misfit Layer Chalcogenides, [(MX)ⁿ]^{1+x}(TX²)^m: a Key for Understanding their Stability and Properties. Molecular Crystals and Liquid Crystals, 2000, 341, 1-8.	0.3	27
143	Re-examination of yushkinite: chemical composition, optical properties and interlayer charge transfer. Mineralogical Magazine, 1999, 63, 879-889.	0.6	5
144	Band structure and electronic properties of the incommensurate misfit compound. Journal of Physics Condensed Matter, 1999, 11, 2887-2900.	0.7	12

#	Article	IF	Citations
145	Evidence of a Mixed-Valence State for Europium in the Misfit Layer Compound [(EuS)1.5]1.15NbS2 by Means of a Superspace Structural Determination, MÃ¶ssbauer Spectroscopy, and Magnetic Measurements. Journal of Solid State Chemistry, 1999, 147, 58-67.	1.4	23
146	Electronic properties of the (las)1.18vs2 incommensurate misfit compound.. Synthetic Metals, 1999, 103, 2640-2643.	2.1	9
147	Synthesis and Structure Determination of La8Ti10S24O4. Journal of Solid State Chemistry, 1998, 136, 46-50.	1.4	21
148	Synthesis and Structure Determination of Sm3NbSe3O4. Journal of Solid State Chemistry, 1998, 137, 122-126.	1.4	12
149	Preparation and crystal structure determination of Eu27Ti20X2S54O12 (X â‰ˆ I0.35 Cl0.65). Comptes Rendus De L'Academie Des Sciences - Series IIc: Chemistry, 1998, 1, 115-121.	0.1	1
150	Stability and charge transfer in the misfit compound (LaS)(SrS)0.2CrS2: Ab initio band-structure calculations. Physical Review B, 1997, 55, 9409-9414.	1.1	31
151	Synthesis and structure determination of a new cerium titanium oxysulfide [Ce20Ti11S44O6]. Materials Research Bulletin, 1997, 32, 1181-1192.	2.7	12
152	A new misfit bilayer compound in the samarium titanium sulfur system. Materials Research Bulletin, 1996, 31, 1307-1316.	2.7	2
153	Incommensurate Structure of a Lillianite-Type Samarium Chromium Sulfide Sm2/3Cr2S4. Journal of Solid State Chemistry, 1996, 127, 295-301.	1.4	10
154	Preparation and Crystal Structure Determination of La20Ti11S44O6. Journal of Solid State Chemistry, 1995, 120, 164-169.	1.4	20